| Name: <br> Enrolment No: |  |  |  |
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| Course: Analog Electronics-I Semester: III <br> Program: B. Tech (ECE) Time: 03 hrs. <br> Course Code: ECEG2011 Max. Marks: 100 <br> Instructions: The QP is $\mathbf{3}$ pages long. Draw the neat and clean diagram wherever it is needed. |  |  |  |
| SECTION A |  |  |  |
| S. No. |  | Marks | CO |
| Q 1 | Given that $\beta_{\mathrm{dc}}=120$ and $\mathrm{I}_{\mathrm{C}}=2.0 \mathrm{~mA}$, find $\mathrm{I}_{\mathrm{E}}$ and $\mathrm{I}_{\mathrm{B}}$. | 4 | CO1 |
| Q 2 | State Miller's theorem with the aid of a circuit diagram. Write the importance of this theorem in circuit analysis. | 4 | CO1 |
| Q 3 | Calculate the power gain in decibels for each of the following cases. <br> (a) $\mathrm{P}_{\mathrm{o}}=100 \mathrm{~W}, \mathrm{P}_{\mathrm{i}}=5 \mathrm{~W}$. <br> (b) $\mathrm{P}_{\mathrm{o}}=100 \mathrm{~mW}, \mathrm{P}_{\mathrm{i}}=5 \mathrm{~mW}$. | 4 | CO 3 |
| Q 4 | For a typical BJT ( $\mathrm{h}_{\mathrm{ie}}=2.4 \mathrm{k}, \mathrm{h}_{\mathrm{fe}}=100, \mathrm{~h}_{\mathrm{re}}=4 \times 10^{-4}$, and $\left.\mathrm{h}_{\mathrm{oe}}=25 \mu \mathrm{~S}\right)$, sketch the following: <br> a. Common-emitter hybrid equivalent model. <br> b. Common-emitter $r_{e}$ equivalent model. | 4 | CO1 |
| Q 5 | A n-channel JFET has device parameters of $\mathrm{I}_{\mathrm{DSS}}=8 \mathrm{~mA}$ and $\mathrm{V}_{\mathrm{P}}=4 \mathrm{~V}$. Sketch the transfer characteristics. | 4 | CO 2 |
| SECTION B |  |  |  |
| Q 6 | Determine $\mathrm{Z}_{\mathrm{i}}, \mathrm{Z}_{\mathrm{o}}$, and $\mathrm{V}_{\mathrm{o}}$ for the network of the following figure if $\mathrm{V}_{\mathrm{i}}=20$ mV . | 10 | CO 2 |


| Q 7 | Three identical cascaded stages have an overall upper 3-db frequency of 20 kHz and a lower $3-\mathrm{dB}$ frequency of 20 Hz . What are $\mathrm{f}_{\mathrm{L}}$ and $\mathrm{f}_{\mathrm{H}}$ of each stage? Assume non-interacting stages. | 10 | $\mathrm{CO4}$ |
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| Q 8 | (a) Compare Field Effect Transistors' (FET) advantages and disadvantages to those of BJTs. <br> (b) Draw the basic construction of a depletion-type MOSFET. What is the effect of $\mathrm{V}_{\mathrm{GS}}$ on channel width? | 5+5 | CO 2 |
| Q 9 | Given that $\mathrm{I}_{\mathrm{CQ}}=2 \mathrm{~mA}$ and $\mathrm{V}_{\mathrm{CEQ}}=10 \mathrm{~V}$ determine $\mathrm{R}_{1}$ and $\mathrm{R}_{\mathrm{C}}$ for the network of following figure | 10 | CO1 |
| SECTION-C |  |  |  |
| Q 10 | (a) What is the significant difference between the construction of an enhancement type MOSFET and a depletion type MOSFET. <br> (b) For the n-channel depletion-type MOSFET of below figure, determine: (i) $I_{D Q}$ and $V_{G S Q}$ (ii) $V_{D S}$ | 5+15 | CO 2 |
| Q 11 | Determine $\mathrm{Z}_{\mathrm{i}}, \mathrm{Z}_{\mathrm{o}}$, and $\mathrm{V}_{\mathrm{o}}$ for the network of following figure if $\mathrm{V}_{\mathrm{i}}=20 \mathrm{mV}$. | 20 | $\mathrm{CO3}$ |



